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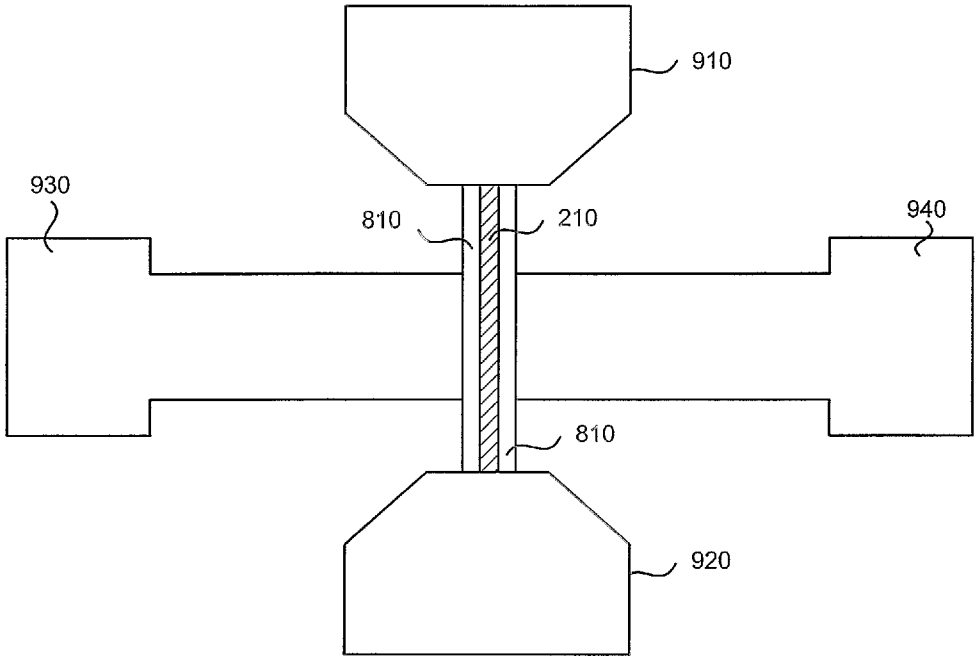
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(54) Title: METHOD FOR FORMING STRUCTURES IN FINFET DEVICES



(57) Abstract: A semiconductor device includes a first fin structure (810), a second fin structure (810), and a third fin structure (210). The first and second fin structures (810) include a single-crystal silicon material. The third fin structure (210) is located between the first fin structure (810) and the second fin structure (810) and includes a dielectric material. The third fin structure (210) causes stress to be induced in the single-crystal silicon material of the first fin structure (810) and the second fin structure (810).

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